

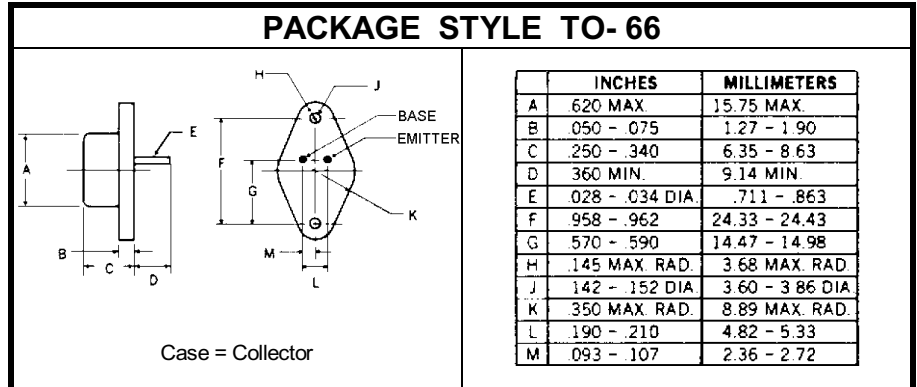
SILICON NPN POWER TRANSISTOR

DESCRIPTION:

The **2N6233** is Designed for General Purpose High Voltage Amplifier and Switching Applications.

MAXIMUM RATINGS

I_C	5.0 A 10 A (PEAK)
V_{CE}	225 V
P_{DISS}	50 W @ T _C = 25 °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +200 °C
θ_{JC}	3.5 °C/W


CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	I _C = 20 mA	225			V
I_{CEO}	V _{CE} = 225 V			1.0	mA
I_{CBO}	V _{CE} = 250 V			0.1	mA
I_{CEX}	V _{CE} = 250 V V _{BE} = -1.5 V T _C = 150 °C			1.0	mA
I_{EBO}	V _{EB} = 6.0 V			0.1	mA
h_{FE}	V _{CE} = 5.0 V I _C = 0.1 A I _C = 1.0 A I _C = 3.0 A	25 25 10		125	---
V_{CE(SAT)}	I _C = 1.0 A I _B = 0.1 A I _C = 5.0 A I _B = 1.0 A			0.5 2.5	V
V_{BE(SAT)}	I _C = 1.0 A I _B = 0.1 A I _C = 5.0 A I _B = 1.0 A			1.0 2.0	V
V_{BE(ON)}	V _{CE} = 5.0 V I _C = 1.0 A			1.0	V
C_{ob}	V _{CB} = 10 V f = 0.1 MHz			200	pF
f_t	V _{CE} = 10 V I _C = 250 mA f = 10 MHz	20			MHz
t_r	V _{CC} = 200 V I _C = 1.0 A, I _{B1} = 0.1 A			0.5	μS
t_s	V _{CC} = 200 V I _C = 1.0 A, I _{B1} = 0.1 A			3.5	μS
t_f	V _{CC} = 200 V I _C = 1.0 A, I _{B1} = 0.1 A			0.5	μS